

## 1. RF PERFORMANCE SPECIFICATIONS (Ta= 25°C)

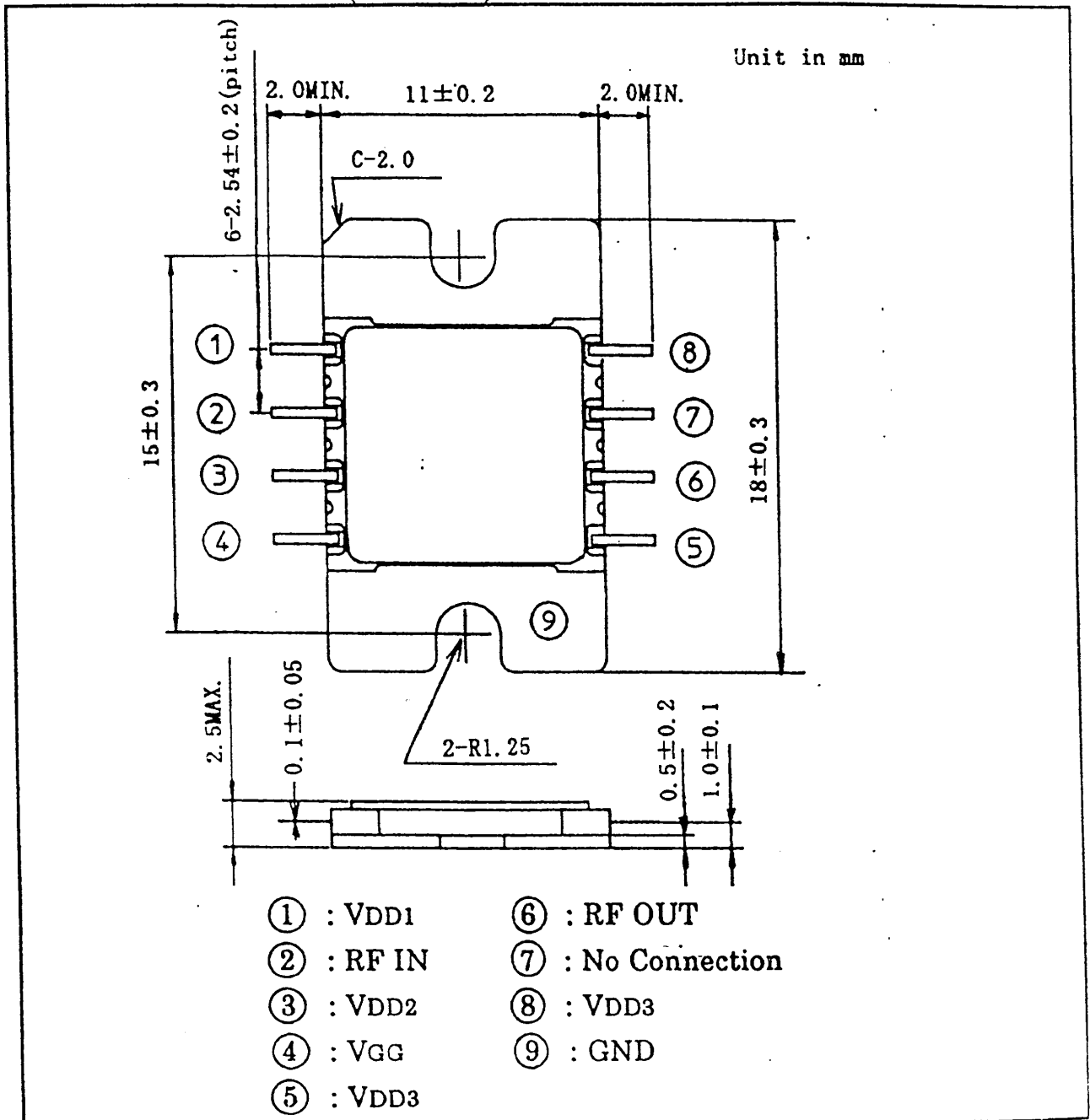
CHARACTERISTICS	SYMBOL	CONDITION	MIN.	TYP.	MAX.	UNIT
Output Power	P <sub>o</sub>	V <sub>DD1</sub> =V <sub>DD2</sub> =V <sub>DD3</sub> =10V	37.0	38.0	—	dBm
Power Gain	G <sub>p</sub>	V <sub>GG</sub> =-5V, f = 1.9 GHz P <sub>in</sub> =7dBm	30.0	31.0	—	dB
Drain Current	I <sub>DD</sub>		—	3.2	3.5	A
Adjacent Channel Leakage Power	P <sub>adj</sub>	V <sub>DD1</sub> =V <sub>DD2</sub> =V <sub>DD3</sub> =10V V <sub>GG</sub> =-5V, f = 1.9 GHz P <sub>o</sub> =37dBm π/4-QPSK Modulation 600MHz Offset	—	-67	—	dBc

## 2. ABSOLUTE MAXIMUM RATINGS (Ta= 25°C)

CHARACTERISTICS	SYMBOL	UNIT	RATINGS
Drain Supply Voltage	V <sub>DD1</sub> , V <sub>DD2</sub> , V <sub>DD3</sub>	V	15
Gate Supply Voltage	V <sub>GG</sub>	V	-15
Input Power	P <sub>in</sub>	dBm	16
Flange Temperature	T <sub>f</sub>	°C	-30 · +80
Storage Temperature	T <sub>stg</sub>	°C	-65 · +175

PRELIMINARY

PACKAGE OUTLINE (2-11E1A)



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